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				Application Number	10/582,035-Conf. #1665
				Filing Date	May 7, 2007
				First Named Inventor	Shen
				Art Unit	4146
				Examiner Name	R. T. Huber
Sheet	1	of	1	Attorney Docket Number	GWS-009

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
/R.H./	A16*	US-6,507,070	01-14-2003	Shen et al.	
FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
/R.H./	C6	Darwish, et al., "Scaling Issues in Lateral Power MOSFETS," Proc. 1998 Intl. Symp. on Power Semiconductor Devices & ICs, pp. 329-332.			
/R.H./	C7	Shen et al., "Lateral Discrete Power MOSFET: Enabling Technology for Next-Generation, MHz-Frequency, High-Density DC/DC Converters," APEC (2004).			
/R.H./	C8	Sun et al., "0.35 $\mu$ m, 43 $\mu$ Ωcm <sup>2</sup> 6mΩ Power MOSFET to Power Future Microprocessor," IEEE pp. 77-79 (1999).			
/R.H./	C9	Pavier et al., "Bi-directional FlipFET™ MOSFETs for Cell Phone Battery Protection Circuits," PCIM 2001.			
Examiner Signature	/Robert Huber/			Date Considered	02/05/2009

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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